# **MMBT5401**



### MMBT5401 SOT-23 Plastic-Encapsulate Transistors(PNP)

#### **General description**

SOT-23 Plastic-Encapsulate Transistors(PNP)

#### FEATURES

- Complementary to MMBT5551
- Power Dissipation of 300mW
- High Stability and High Reliability
- SOT-23 Small Outline Plastic Package
- Epoxy UL: 94V-0

SOT-23 1. BASE 2. EMITTER 3. COLLECTOR

#### **DEVICE MARKING CODE:**

Device Type	Device Marking
MMBT5401	2L

. Maximum Ratings & Thermal Characteristics (Ratings at 25°C ambient temperature unless otherwise specified.)

Parameters	Symbol	Value	Unit	
Collector-Base Voltage	Vсво	-160	V	
Collector-Emitter Voltage	VCEO	-150	V	
Emitter -Base Voltage	Vebo	-5	V	
Collector Current-Continuous	lc	-600	mA	
Collector Power Dissipation	Pc	300	mW	
Junction Temperature	Tj	150	°C	
Storage Temperature	Tstg	-55-+150	°C	
Thermal resistance From junction to ambient	Reja	416	°C <b>/W</b>	

#### Electrical Characteristics (Ratings at 25°C ambient temperature unless otherwise specified).

Parameter	Symbols	Test Condition	Limits		Unit
			Min	Max	Unit
Collector-base breakdown voltage	V(BR)CBO	IC=-100uA, IE=0	-160		V
Collector-emitter breakdown voltage	V(BR)CEO *	IC=-1mA, IB=0	-150		V
Emitter-base breakdown voltage	V(BR)EBO	IE=-10uA, IC=0	-5		V
Collector cut-off current	Ісво	VCB=-120V, IE=0		-100	nA
Emitter cut-off current	IEBO	VEB=-4V, IC=0		-100	nA
	hFE(1) *	VCE=-5V, IC=-1mA	80		
DC current gain	hFE(2) *	VCE=-5V, IC=-10mA	100	300	
	hFE(3) *	VCE=-5V, IC=-50mA	30		
Collector-emitter saturation voltage	VCE(sat)1 *	IC=-10mA, IB=-1mA		-0.2	V
	VCE(sat)2 *	IC=-50mA, IB=-5mA		-0.5	V
Base -emitter saturation voltage	VBE(sat)1 *	IC=-10mA, IB=-1mA		-1.00	V
	VBE(sat)2 *	IC=-50mA, IB=-5mA		-1.00	V
Transition frequency	fT	VCE=-5V, IC=10mA,f=30MHz	100		MHz

\*Pulse test: pulse width  $\leq$  300us, duty cycle  $\leq$  2.0%

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#### **CLASSIFICATION OF hFE(1)**

HFE	100-300		
RANK	L	Н	
RANGE	100-200	200-300	

#### Static Characteristic hre ١, -20 580 Vce=-5V -100uA COMMON 118 EMITTER T\_=100 °C T,=25°C -90uA 250 (Mul) -\$15 -BOuA # 28 -14 -70uA 20 DC CURRENT GAN COLLECTOR CURRENT -12 - - 60uA 10 150 T\_=25 °C -50uA -8 -40uA 100 -6 \*\*1\*\* -30uA 4 50 -20uA 2 I\_=-10uA -0 8 -10 COLLECTOR CURRENT -4 -100 -11 -3 ×ð I (mA) COLLECTOR-EMITTER VOLTAGE Voz (V) VEEsat VCEsat 1 I, -1.0 -1 β=10 β=10 COLLECTOR-EMITTER SATURATION VOLTAGE Vola (V) T\_=25°C -0.8 BASE-EMITTER SATURATION VOLTAGE V<sub>RM</sub> (V) T\_=100°C -0.6 111 -0.1 1110 T\_=100°C -0 T =25°C -8.2 -0.0 L -0.1 -0.01 100 -10 100 -1 COLLECTOR CURRENT I (mA) COLLECTOR CURRENT Ic (mA) ۱<sub>с</sub> V. C ... / C. V<sub>CB</sub> / V<sub>EB</sub> -160 100 V<sub>ct</sub>=-5V f=1MHz 1=0/1=0 (mA) T\_=25 °C G Ch DOLLECTOR CURRENT -10 CAPACITANCE C T\_=100 °C 10 T\_=25°C -1 Cob -0.0 -0.5 -0.2 -1.0 -0.4 -0.6 -0.8 -1 -10 REVERSE VOLTAGE V (V)

**RATING AND CHARACTERISTIC CURVES** 

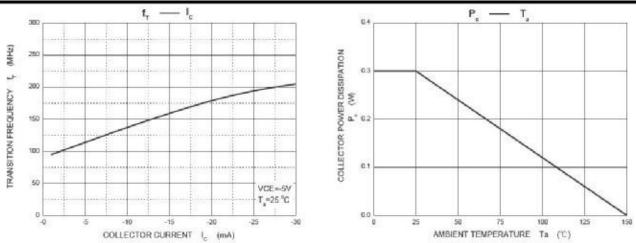
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BASE-EMITTER VOLTAGE

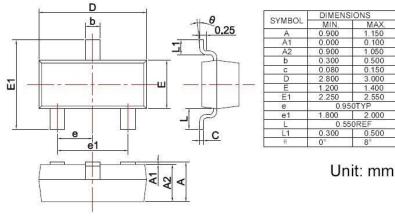
 $V_{gg}(V)$ 

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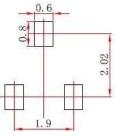


#### SOT-23 PACKAGE OUTLINE Plastic surface mounted package



#### Precautions: PCB Design

Recommended land dimensions for SOT-23 diode. Electrode patterns for PCBs



Note: 1.Controlling dimension:In millimeters. 2.General tolerance:± 0.05mm. 3.The pad layout is for reference purposes only.



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